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ABSTRACT OF THE DISCLOSURE

5 A method for fabricating a BiCMOS integrated circuit. The method includes the steps of forming in a single implantation step a base region 211 of a bipolar transistor and a p-well 212 of an n-channel MOS transistor; and forming in a single implantation step a collector contact well 213 of a bipolar transistor and an n-well 208 of a p-channel MOS transistor.

10